

1740nm InGaAs 2000um PD Chip datasheet

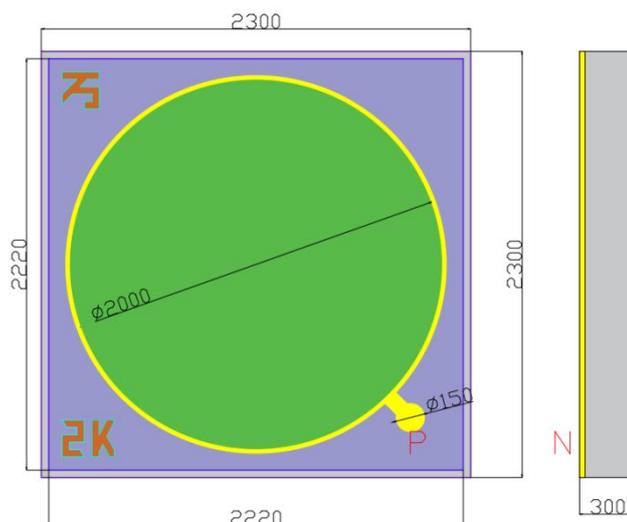
P/N : WIR3-2000

Feature

High responsivity
Low dark current
900-1740nm Spectral range

Structure

InGaAs / InP PIN Chip.
P Electrode (anode) : Gold.
N Electrode (cathode) : Gold.



DIMENSIONS

Conditions	Min.	Typ.	Max	Unit
Active	-	2000	-	μm
Chip width	2250	2300	2350	μm
Chip length	2250	2300	2350	μm
Chip height	280	300	320	μm
Pad Area	140	150	160	μm

Electro-Optical Characteristics (@ Ta=25 °C)

Parameter	Symbol	Test Condition	Min.	Typ.	Max.	Unit
Dark current	Id	Vr=-1V		5	25	nA
Reverse Breakdown	Vbr	Ir=-10μA	6	-	-	V
Responsivity	R	Vr=0V,@1653 nm	0.9	0.95	-	A/W
Capacitance	Cp	Vr=1V, f=1MHz		550	1000	pF
Wavelength range	λ		900	1650	1740	nm

ABSOLUTE MAXIMUM RATING

Parameter	Rating
Operating Temperature	-40°C to 85°C
Storage Temperature	-55°C to 125°C
Forward Current	10mA

